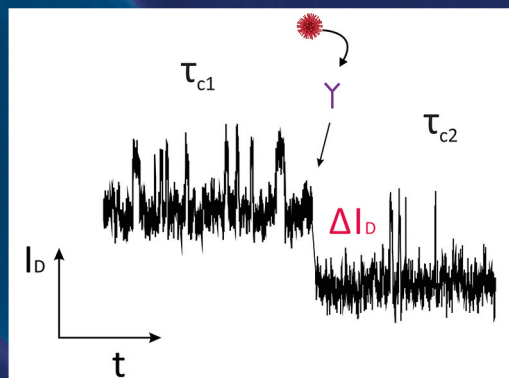
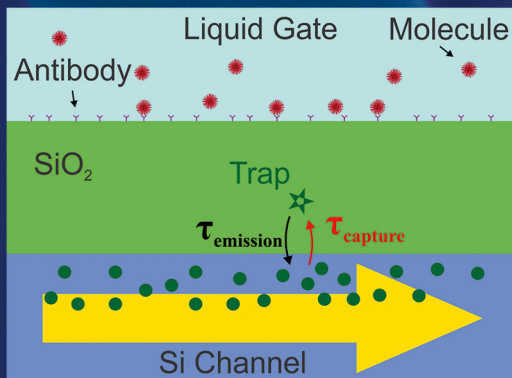


Transport and Noise Properties of Nanostructure Transistors for Biosensor Applications

Jing Li



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